

HT7022A 2.2V Voltage Detector

Features

- Low detectable voltage 2.2V
- · Low power consumption
- · Low temperature coefficient

- Built-in high-stability reference source
- · Built-in hysteresis characteristic
- TO-92 and SOT-89 package

Applications

- · Battery checkers
- Power failure detectors
- · Microcomputer reset

- · Battery memory backup
- · Non-volatile RAM signal storage protectors

General Description

The HT7022A is a three-terminal low power voltage detector implemented in CMOS technology. It detects a particular fixed voltage 2.2V. The voltage detector consists of a high-precision and low power consumption standard voltage source, a comparator, hysteresis circuit, and an output driver. CMOS technology ensures low power consumption.

Although designed primarily as fixed voltage detectors, these devices can be used with external components to detect user specified threshold voltages (NMOS open drain type only).

Output Type Selection Table

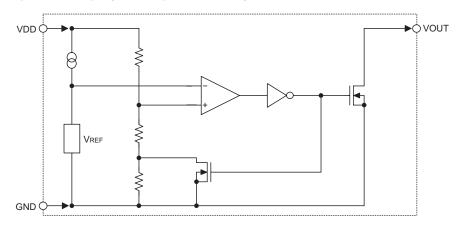
V _{DD} Type V _{OUT}	V _{DD} >V _{DET} (+)	V _{DD} ≤V _{DET} (−)
A	Hi-Z	VSS

Rev. 1.10 1 April 20, 2004

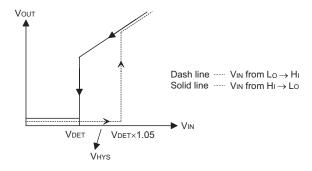


Block Diagram

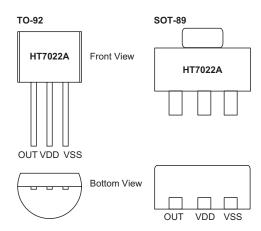
N Channel Open Drain Output (Normal Open; Active Low)



A Type

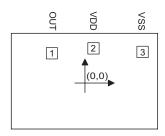


Pin Assignment





Pad Assignment



Chip size: $2032 \times 1321 \; (\mu m)^2$

Pad Coordinates

Unit:	μm
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Pad No.	Х	Υ
1	-434.34	394.97
2	120.65	461.01
3	774.70	412.75

Absolute Maximum Ratings

Supply VoltageV _{SS} -0.3V to V _{SS} +13V	Output VoltageV _{SS} -0.3V to V _{DD} +0.3V
Output Current50mA	Storage Temperature50°C to 125°C
Power Consumption200mW	Operating Temperature40°C to 85°C

Note: These are stress ratings only. Stresses exceeding the range specified under "Absolute Maximum Ratings" may cause substantial damage to the device. Functional operation of this device at other conditions beyond those listed in the specification is not implied and prolonged exposure to extreme conditions may affect device reliability.

Electrical Characteristics

Ta=25°C

Symbol Parameter		Test Conditions		Min.	Trem	Max.	Unit
Symbol	Parameter	V_{DD}	Conditions	IVIIII.	Тур.	IVIAX.	Onit
\/	Hi→Lo Detectable Voltage	_	_	2.09	2.2	2.31	V
V _{DET}	Lo→Hi Detectable Voltage	_	_	2.132	2.31	2.541	V
V _{HYS}	Hysteresis Width	_	_	0.02V _{DET}	0.05V _{DET}	0.1V _{DET}	V
I _{DD}	Operating Current	3.2V	No load	_	1.8	4	μА
V_{DD}	Operating Voltage	_	_	1.6	_	12	V
I _{OL}	Output Sink Current	2V	V _{OUT} =0.2V	0.5	1	_	mA
$\frac{\Delta V_{DET}}{\Delta T_{a}}$	Temperature Coefficient	_	0°C <ta<70°c< td=""><td>_</td><td>±0.9</td><td>_</td><td>mV/°C</td></ta<70°c<>	_	±0.9	_	mV/°C

^{*} The IC substrate should be connected to VDD in the PCB layout artwork.



Functional Description

The HT7022A is a voltage detector equipped with a high stability voltage reference which is connected to the negative input of a comparator—denoted as V_{REF} in the following figure for NMOS output voltage detector.

When the voltage drop to the positive input of the comparator (i,e,V_B) is higher than $V_{REF},\ VOUT$ goes high, M1 turns off, and V_B is expressed as $V_{BH} = V_{DD} \times (R_B + R_C) / (R_A + R_B + R_C)$. If V_{DD} is decreased so that V_B falls to a value less than $V_{REF},$ the comparator output inverts from high to low, V_{OUT} goes low, V_C is high, M1 turns on, RC is bypassed, and V_B becomes: $V_{BL} = V_{DD} \times R_B / (R_A + R_B),$ which is less than V_{BH} . By so doing, the comparator output will stay low to prevent the circuit from oscillating when $V_B \approx V_{REF}$.

If V_{DD} falls below the minimum operating voltage, the output becomes undefined. When VDD goes from low to $V_{DD} \times R_B$ / $(R_A + R_B) > V_{REF}$, the comparator output and V_{OUT} goes high.

The detectable voltage is defined as:

$$V_{DET} (-) = \frac{R_A + R_B + R_C}{R_B + R_C} \times V_{REF}$$

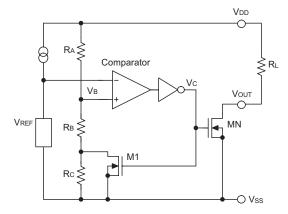
The release voltage is defined as:

$$V_{DET}$$
 (+) = $\frac{R_A + R_B}{R_B} \times V_{REF}$

The hysteresis width is:

$$V_{HYS} = V_{DET}(+) - V_{DET}(-)$$

The figure demonstrates the NMOS output type with positive output polarity (V_{OUT} is normally open, active low).



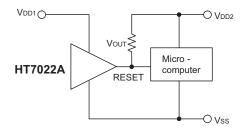
NMOS Output Voltage Detector

Application Circuits

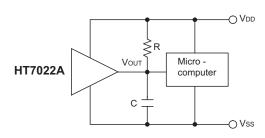
Microcomputer Reset Circuit

Normally a reset circuit is required to protect the microcomputer system from malfunctions due to power line interruptions. The following examples show how different output configurations perform a reset function in various systems.

 NMOS open drain output application for separate power supply



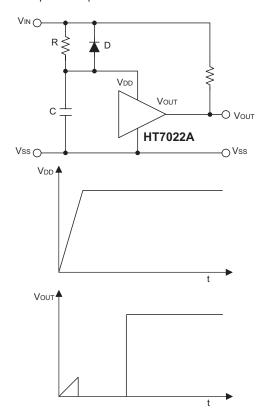
• NMOS open drain output application with R-C delay





Power-on Reset Circuit

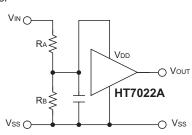
With several external components, the HT7022A can be used to perform a power-on reset function as shown:



Change of Detectable Voltage

If the required voltage is not found in the standard product selection table, it is possible to change it by using external resistance dividers or diodes.

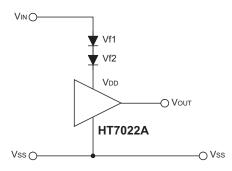
• Varying the detectable voltage with a resistance divider



Detectable voltage =
$$\frac{R_A + R_B}{R_B} \times V_{DET}$$

$$Hysteresis \ width = \frac{R_{\text{A}} + R_{\text{B}}}{R_{\text{B}}} \times V_{\text{HYS}}$$

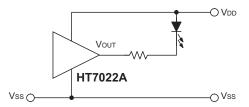
· Varying the detectable voltage with a diode



Detectable Voltage = $V_{f1}+V_{f2}+V_{DET}$

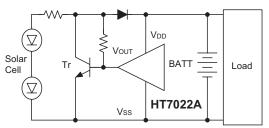
Malfunction Analysis

The following circuit demonstrates the way a circuit analyzes malfunctions by monitoring the variation or spike noise of power supply voltage.



Charge Monitoring Circuit

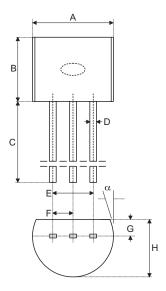
The following circuit shows a charged monitor for protection against battery deterioration by overcharging. When the voltage of the battery is higher than the set detectable voltage, the transistor turns on to bypass the charge current, protecting the battery from overcharging.





Package Information

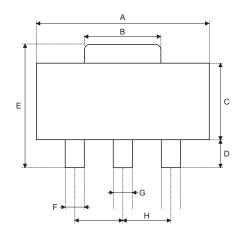
3-pin TO-92 Outline Dimensions

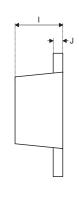


Symbol	Dimensions in mil			
Symbol	Min.	Nom.	Max.	
Α	170	_	200	
В	170	_	200	
С	500	_	_	
D	11	_	20	
E	90	_	110	
F	45	_	55	
G	45	_	65	
Н	130	_	160	
I	8	_	18	
α	4 °	_	6°	



3-pin SOT-89 Outline Dimensions



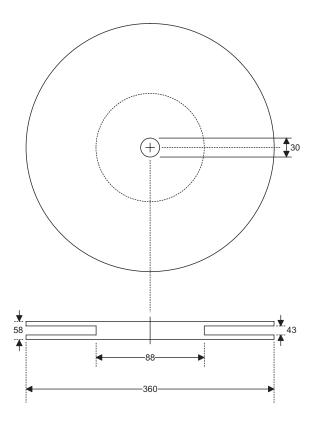


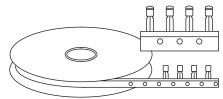
Symbol		Dimensions in mil		
Symbol	Min.	Nom.	Max.	
Α	173	_	181	
В	64	_	72	
С	90	_	102	
D	35	_	47	
E	155	_	167	
F	14	_	19	
G	17	_	22	
Н	_	59	_	
I	55	_	63	
J	14	_	17	



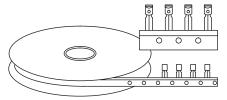
Product Tape and Reel Specifications

TO-92 Reel Dimensions (Unit: mm)





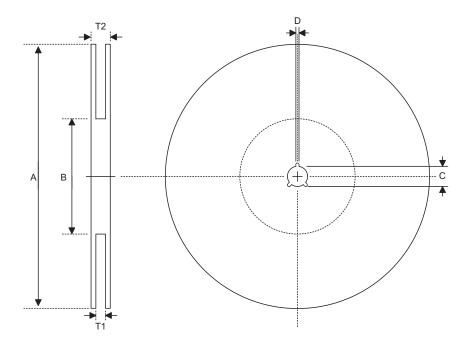
Package Up, Flat Side Up



Package Up, Flat Side Down



SOT-89 Reel Dimensions

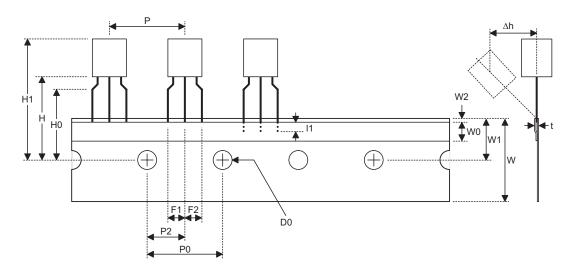


SOT-89

Symbol	Description	Dimensions in mm
Α	Reel Outer Diameter	180±1.0
В	Reel Inner Diameter	62±1.5
С	Spindle Hole Diameter	12.75+0.15
D	Key Slit Width	1.9±0.15
T1	Space Between Flange	12.4+0.2
T2	Reel Thickness	17–0.4



TO-92 Carrier Tape Dimensions



TO-92

Symbol	Description	Dimensions in mm
I1	Taped Lead Length	(2.5)
Р	Component Pitch	12.7±1.0
P ₀	Perforation Pitch	12.7±0.3
P ₂	Component to Perforation (Length Direction)	6.35±0.4
F ₁	Lead Spread	2.5+0.4 -0.1
F ₂	Lead Spread	2.5+0.4 -0.1
Δh	Component Alignment	0±0.1
W	Carrier Tape Width	18.0+1.0 -0.5
W ₀	Hold-down Tape Width	6.0±0.5
W ₁	Perforation Position	9.0±0.5
W ₂	Hold-down Tape Position	(0.5)
H ₀	Lead Clinch Height	16.0±0.5
H ₁	Component Height	Less than 24.7
D ₀	Perforation Diameter	4.0±0.2
t	Taped Lead Thickness	0.7±0.2
Н	Component Base Height	19.0±0.5

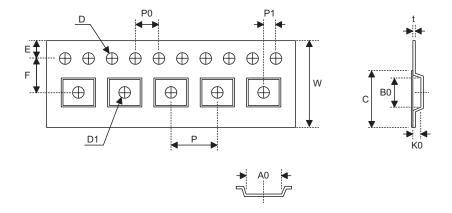
Note: Thickness less than 0.38±0.05mm~0.5mm

P0 Accumulated pitch tolerance: ± 1 mm/20pitches.

() Bracketed figures are for consultation only



SOT-89 Carrier Tape Dimensions



SOT-89

Symbol	Description	Dimensions in mm
W	Carrier Tape Width	12.0+0.3 -0.1
Р	Cavity Pitch	8.0±0.1
E	Perforation Position	1.75±0.1
F	Cavity to Perforation (Width Direction)	5.5±0.05
D	Perforation Diameter	1.5+0.1
D1	Cavity Hole Diameter	1.5+0.1
P0	Perforation Pitch	4.0±0.1
P1	Cavity to Perforation (Length Direction)	2.0±0.10
A0	Cavity Length	4.8±0.1
В0	Cavity Width	4.5±0.1
K0	Cavity Depth	1.8±0.1
t	Carrier Tape Thickness	0.30±0.013
С	Cover Tape Width	9.3



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